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# N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>(BR)DSS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)	
100	0.085 at V <sub>GS</sub> = 10 V	20 <sup>a</sup>	

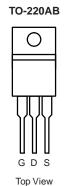
### **FEATURES**

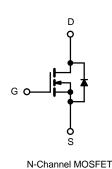
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- · Low Thermal Resistance Package
- 100 % R<sub>g</sub> and UIS Tested



### **APPLICATIONS**

• Isolated DC/DC Converters





**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25$  °C, unless otherwise noted Parameter Symbol Limit Unit Drain-Source Voltage  $V_{DS}$ 100 ٧ ± 20 Gate-Source Voltage  $V_{GS}$ T<sub>C</sub> = 25 °C 20<sup>a</sup> Continuous Drain Current (T<sub>J</sub> = 175 °C)  $I_D$ T<sub>C</sub> = 125 °C 11<sup>a</sup> Α **Pulsed Drain Current**  $I_{DM}$ 80 Avalanche Current  $I_{AS}$ L = 0.1 mH $\mathsf{E}_{\mathsf{AS}}$ 27 Single Pulse Avalanche Energy<sup>b</sup> mJ  $T_C = 25$  °C 70<sup>c</sup> Maximum Power Dissipation<sup>b</sup>  $\mathsf{P}_\mathsf{D}$ W  $T_A = 25 \, ^{\circ}C^d$ 3.3 °C Operating Junction and Storage Temperature Range  $T_J$ ,  $T_{stg}$ - 55 to 175

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient	R <sub>thJA</sub>	55	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.5	C/ V V		

#### Notes:

- a. Package limited.
- b. Duty cycle  $\leq$  1 %.
- c. See SOA curve for voltage derating.
- d. When Mounted on 1" square PCB (FR-4 material).



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	100			3 V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		$V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A		0.085	0.105	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D} = 8 \text{ A}$		15		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			1883		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V, f = 1 MHz		406		
Reverse Transfer Capacitance	C <sub>rss</sub>			60		
Total Gate Charge <sup>c</sup>	$Q_g$			33		nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, \ V_{GS} = 10 \text{ V}, \ I_D = 8 \text{ A}$		11		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			17		
Gate Resistance	$R_g$			1.8		Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			34		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V},  R_{L} = 1.5 \Omega$		250		nc
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 8 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		55		ns
Fall Time <sup>c</sup>	t <sub>f</sub>			210		
Source-Drain Diode Ratings and Cha	aracteristics 7	<sub>C</sub> = 25 °C <sup>b</sup>				
Continuous Current	I <sub>S</sub>				20	_
Pulsed Current	I <sub>SM</sub>				80	А
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		0.7	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		130		ns
Reverse Recovery Charge	Q <sub>rr</sub>	1- 20 π, απαι – 100 πμο		349		nC

### Notes:

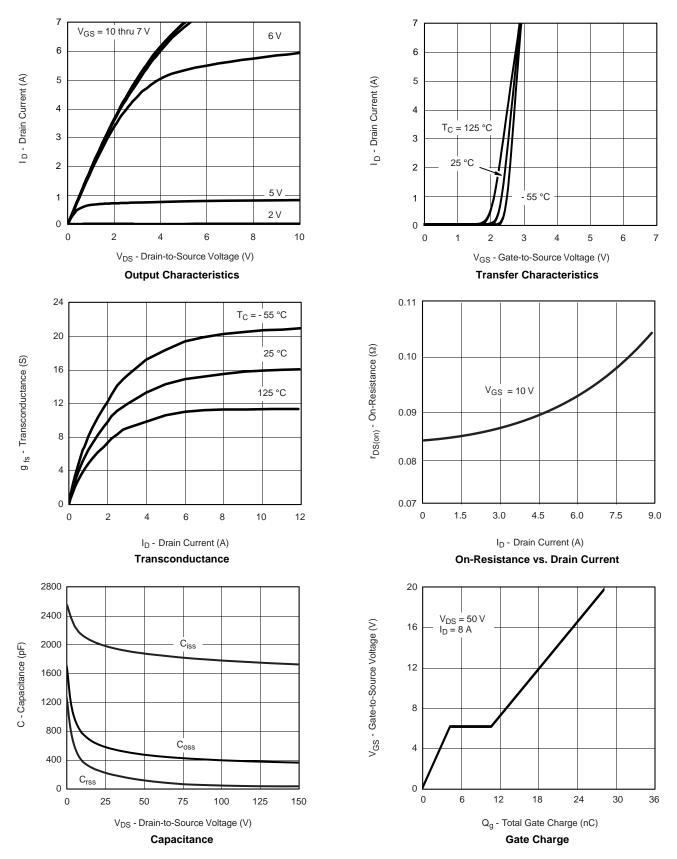
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



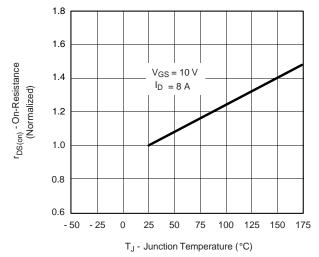


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

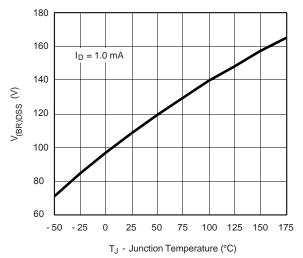




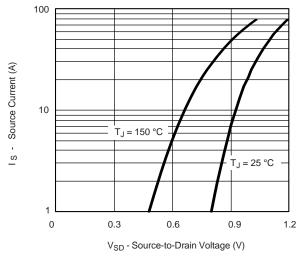
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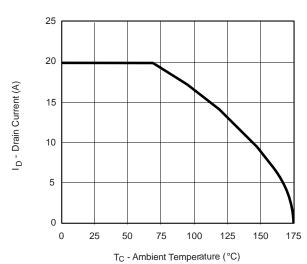
On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature



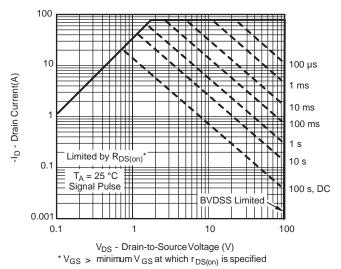
Source-Drain Diode Forward Voltage



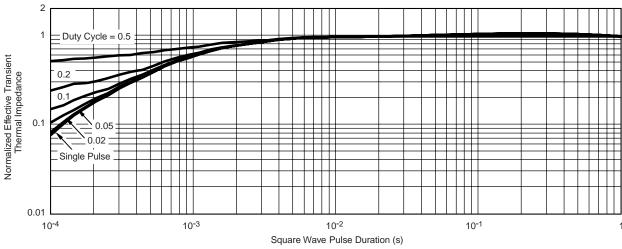
Maximum Avalanche and Drain Current vs. Case Temperature



### THERMAL RATINGS



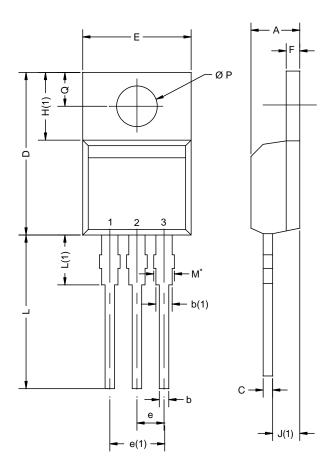
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-220AB**



	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

### Notes

 $<sup>^{*}</sup>$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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